In the Claims

Please cancel claims 11, 12, 13 and 14 without prejudice or disclaimer to the subject matter contained therein.

Please amend the claims as follows:

4.(Amended) The device of claim 1, wherein the semiconductor layer comprises:

a first layer on the insulation layer;

an etch stop layer on the first layer; and

a second layer over the first layer and the etch stop layer.

5. (Amended) The device of claim 1, further comprising a light shielding layer below the gate electrode.

6. (Amended) A method of forming liquid crystal display (LCD) device, the method comprising:

forming a substrate;

forming a gate electrode over the substrate;

forming an insulation layer on the gate electrode and the substrate;

forming a semiconductor layer, aligned relative to the gate electrode, on the insulating layer;

forming a source electrode and a drain electrode electrically connected with the semiconductor layer;

forming a color filter layer on and in direct contact with the source and the drain electrodes;

forming a planarization layer over the color filter layer and the source and drain electrodes, the planarization layer having an opening exposing the drain electrode thereunder; and

forming a pixel electrode on the planarization layer and electrically connected with the drain electrode via the opening in the planarization layer.

7. (Amended) The method of claim 6, wherein the color filter layer is formed to substantially cover the source and drain electrodes to prevent light leakage.

10. (Amended) The method of claim 6, further comprising a step of forming a light shielding layer below the gate electrode.

16. (Amended) The liquid crystal display device of claim 15, wherein the TFT further includes:

a gate insulating layer on the substrate and covering the gate electrode; and

a semiconductor layer formed on the gate insulating layer, having an amorphous silicon layer and a doped amorphous silicon layer,

wherein the gate electrode is formed on the substrate, while the source and drain electrodes are spaced apart from one another and overlap end portions of the doped amorphous silicon layer, respectively.

18. (Amended) The liquid crystal display device of claim 15, further comprising:

a light shielding layer formed between the substrate and the TFT; and

an insulating layer covering the light shielding layer.

19. (Amended) The liquid crystal display device of claim 15, wherein the TFT further includes:

an active layer having source and drain regions at end portions;

a gate insulating layer on a central portion of the active layer, the gate electrode being formed on the gate insulating layer; and

an interlayer insulator formed entirely over the substrate, having a first and a second contact hole which respectively expose a portion of the source and drain regions therebelow,

R 11 Cont.

wherein the source and drain electrodes are formed on the interlayer insulator to respectively contact the source and drain regions.